

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise stated)

| Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|--|--|------|------|------|------|
| BV _{DSS} Drain-Source Breakdown Voltage | V _{GS} = 0 I _D = 10mA | 70 | | | V |
| I _{DSS} Zero Gate Voltage Drain Current | V _{DS} = 28V V _{GS} = 0 | | | 1 | mA |
| I _{GSS} Gate Leakage Current | V _{GS} = 20V V _{DS} = 0 | | | 1 | μA |
| V _{GS(th)} Gate Threshold Voltage* | I _D = 10mA V _{DS} = V _{GS} | 1 | | 7 | V |
| g _{fs} Forward Transconductance* | V _{DS} = 10V I _D = 1A | 0.8 | | | S |
| G _{PS} Common Source Power Gain | V _{DS} = 28V I _{DQ} = 0.1A P _O = 4W f = 200MHz | 13 | | | dB |
| η Drain Efficiency | | 40 | | | % |
| VSWR Load Mismatch Tolerance | | 20:1 | | | — |
| C _{iss} Input Capacitance | V _{DS} = 0V V _{GS} = -5V f = 1MHz | | | 60 | pF |
| C _{oss} Output Capacitance | V _{DS} = 28V V _{GS} = 0 f = 1MHz | | | 30 | |
| C _{rss} Reverse Transfer Capacitance | V _{DS} = 28V V _{GS} = 0 f = 1MHz | | | 2.5 | |

* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

THERMAL DATA

| | | |
|-----------------------|------------------------------------|--------------|
| R _{THj-case} | Thermal Resistance Junction – Case | Max. 2°C / W |
|-----------------------|------------------------------------|--------------|